7. The lipseal assembly of Claim 1, wherein the elastomeric lipseal comprises a first inner diameter defining a substantially circular perimeter for excluding the plating solution from the peripheral region, and wherein the first exposed portion of the one or more contact elements defines a second inner diameter that is larger than the first inner diameter.

8. The lipseal assembly of Claim 7, wherein the magnitude of the difference between the first inner diameter and the second inner diameter is about or less than 0.5mm.

9. The lipseal assembly of Claim 8, wherein the magnitude of the difference between the first inner diameter and the second inner diameter is about or less than 0.3mm.

~~10. A lipseal assembly for use in an electroplating clamshell for engaging and~~ supplying electrical current to a semiconductor substrate during electroplating, the lipseal assembly comprising:

an elastomeric lipseal for engaging the semiconductor substrate during electroplating, wherein upon engagement the elastomeric lipseal substantially excludes plating solution from a peripheral region of the semiconductor substrate; and

one or more flexible contact elements for supplying electrical current to the semiconductor substrate during electroplating, at least a portion of the one or more flexible contact elements conformally positioned on an upper surface of the elastomeric lipseal, and wherein upon engagement with the semiconductor substrate the flexible contact elements are configured to flex and form a conformal contact surface that interfaces with the semiconductor substrate.

11. The lipseal assembly of Claim 10, wherein the conformal contact surface interfaces with a bevel edge of the semiconductor substrate.

12. The lipseal assembly of Claim 10, wherein the one or more flexible contact ~~elements have a portion which is not configured to contact the substrate when the~~

substrate is engaged by the lipseal assembly, and wherein the non-contacting portion comprises a non-conformable material.

13. The lipseal assembly of Claim 10, wherein the conformal contact surface forms a continuous interface with the semiconductor substrate.

14. The lipseal assembly of Claim 10, wherein the conformal contact surface forms a non-continuous interface with the semiconductor substrate having gaps.

15. The lipseal assembly of Claim 14, wherein the one or more flexible contact elements comprise multiple wire tips or a wire mesh disposed on the surface of the elastomeric lipseal.

16. The lipseal assembly of Claim 10, wherein the one or more flexible contact elements conformally positioned on the upper surface of the elastomeric lipseal comprise conductive deposits formed using one or more techniques selected from the group consisting of: chemical vapor deposition, physical vapor deposition, and electroplating.

17. The lipseal assembly of Claim 10, wherein the one or more flexible contact elements conformally positioned on the upper surface of the elastomeric lipseal comprise an electrically conductive elastomeric material.

18. An elastomeric lipseal for use in an electroplating clamshell for supporting, aligning, and sealing a semiconductor substrate in the electroplating clamshell, the lipseal comprising:

a flexible elastomeric support edge comprising a sealing protrusion configured to support and seal the semiconductor substrate wherein, upon sealing the substrate, the sealing protrusion defines a perimeter for excluding plating solution; and

a flexible elastomeric upper portion located above the flexible elastomeric support edge, the flexible elastomeric upper portion comprising:

a top surface configured to be compressed; and

an inner side surface located outward relative to the sealing protrusion, the inner side surface configured to move inward and align the semiconductor substrate upon compression of the top surface.

19. The elastomeric lipseal of Claim 18, wherein at least a portion of the inner side surface is configured to move inward by about or at least 0.2mm upon compression of the top surface.

20. The elastomeric lipseal of Claim 18, wherein when the top surface is not compressed, the inner side surface is located sufficiently outward to allow the semiconductor substrate to be lowered through the flexible elastomeric upper portion and placed onto the sealing protrusion without contacting the upper portion, but wherein upon placement of the semiconductor substrate on the sealing protrusion and compression of the top surface, the inner side surface contacts and pushes on the semiconductor substrate aligning the semiconductor substrate in the electroplating clamshell.

21. A method of aligning and sealing a semiconductor substrate in an electroplating clamshell having an elastomeric lipseal, the method comprising:

opening the clamshell;

providing a substrate to the clamshell;

lowering the substrate through an upper portion of the lipseal and onto a sealing protrusion of the lipseal;

compressing a top surface of the upper portion of the lipseal to align the substrate; and

pressing on the substrate to form a seal between the sealing protrusion and the substrate.

22. The method of Claim 21, wherein compressing the top surface of the upper portion of the lipseal causes an inner side surface of the upper portion of the lipseal to push on the substrate aligning it in the clamshell.

23. The method of Claim 21, wherein compressing the top surface to align the substrate comprises pressing on the top surface with a first surface of the cone of the clamshell, and wherein pressing on the substrate to form a seal comprises pressing on the substrate with a second surface of the cone of the clamshell.

24. The method of Claim 21, wherein compressing the top surface to align the substrate comprises pushing on the top surface with a first pressing component of the clamshell, and wherein pressing on the substrate to form a seal comprises pressing on the substrate with a second pressing component of the clamshell, the second pressing component independently movable with respect to the first pressing component.

25. The method of Claim 24, wherein compressing the top surface comprises adjusting the pressing force exerted by the first pressing component based upon the diameter of the semiconductor substrate.